Preferred Device

# **Complementary Silicon Plastic Power Transistors**

# TO-220, NPN & PNP Devices

Complementary silicon plastic power transistors are designed for use as high-frequency drivers in audio amplifiers.

#### **Features**

- h<sub>FE</sub> = 100 (Min) @ I<sub>C</sub> = 0.5 Adc = 10 (Min) @ I<sub>C</sub> = 2.0 Adc
- Collector–Emitter Sustaining Voltage –

 $V_{CEO(sus)} = 350 \text{ Vdc (Min)} - MJE15034, MJE15035$ 

- High Current Gain Bandwidth Product  $f_T = 30 \text{ MHz}$  (Min) @  $I_C = 500 \text{ mAdc}$
- TO-220AB Compact Package
- Epoxy meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Machine Model: C Human Body Model: 3B
- Pb-Free Packages are Available\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	350	Vdc
Collector-Base Voltage	V <sub>CB</sub>	350	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5.0	Vdc
Collector Current - Continuous - Peak	I <sub>C</sub>	4.0 8.0	Adc
Base Current	Ι <sub>Β</sub>	1.0	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	50 0.40	W W/°C
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	2.0 0.016	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol Max		Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

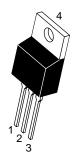
\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



### ON Semiconductor®

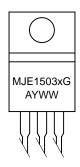
http://onsemi.com

# 4.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 350 VOLTS, 50 WATTS



TO-220AB CASE 221A STYLE 1

#### **MARKING DIAGRAM**



MJE1503x = Device Code x = 4 or 5 A = Location Code

Y = Year WW = Work Week G = Pb-Free Package

#### **ORDERING INFORMATION**

Device	Package	Shipping
MJE15034	TO-220AB	50 Units / Rail
MJE15034G	TO-220AB (Pb-Free)	50 Units / Rail
MJE15035	TO-220AB	50 Units / Rail
MJE15035G	TO-220AB (Pb-Free)	50 Units / Rail

**Preferred** devices are recommended choices for future use and best overall value.

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage (Note 1)	$(I_C = 10 \text{ mAdc}, I_B = 0)$	V <sub>CEO(sus)</sub>	350	_	Vdc
Collector Cutoff Current	$(V_{CB} = 350 \text{ Vdc}, I_{E} = 0)$	I <sub>CBO</sub>	-	10	μAdc
Emitter Cutoff Current	$(V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0)$	I <sub>EBO</sub>	_	10	μAdc
ON CHARACTERISTICS (Note 1)			•	•	•
DC Current Gain	$ \begin{aligned} &(I_{C} = 0.1 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \\ &(I_{C} = 0.5 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \\ &(I_{C} = 1.0 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \\ &(I_{C} = 2.0 \text{ Adc, } V_{CE} = 5.0 \text{ Vdc}) \end{aligned} $	h <sub>FE</sub>	100 100 50 10	- - -	_
Collector-Emitter Saturation Voltage	$(I_C = 1.0 \text{ Adc}, I_B = 0.1 \text{ Adc})$	V <sub>CE(sat)</sub>	-	0.5	Vdc
Base-Emitter On Voltage	$(I_C = 1.0 \text{ Adc}, V_{CE} = 5.0 \text{ Vdc})$	V <sub>BE(on)</sub>	-	1.0	Vdc
DYNAMIC CHARACTERISTICS					-
Current Gain – Bandwidth Product (Note 2) (I <sub>C</sub> = 500 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.0 MHz)		f <sub>T</sub>	30	_	MHz

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

<sup>2.</sup>  $f_T = |h_{fe}| \cdot f_{test}$ .

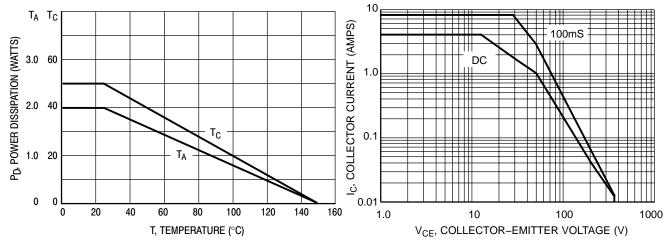


Figure 1. Power Derating

Figure 2. Active Region Safe Operating Area

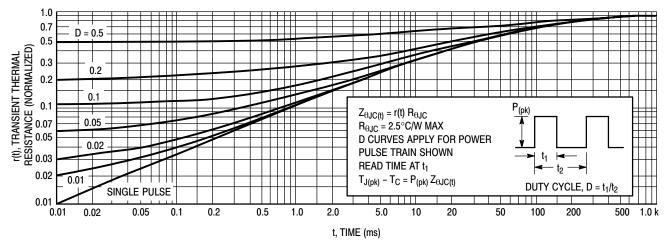


Figure 3. Thermal Response

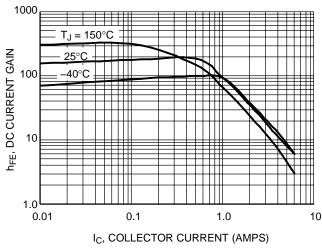


Figure 4. DC Current Gain, V<sub>CE</sub> = 5.0 V **NPN MJE15034** 

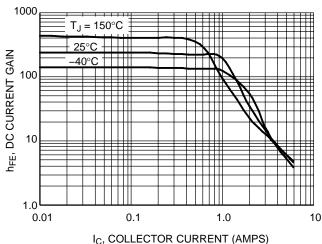


Figure 5. DC Current Gain, V<sub>CE</sub> = 5.0 V **PNP MJE15035** 

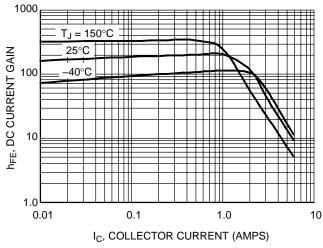


Figure 6. DC Current Gain, V<sub>CE</sub> = 20 V **NPN MJE15034** 

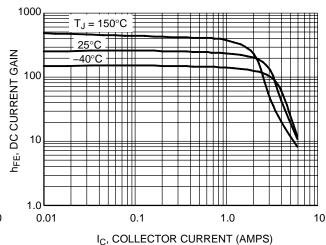


Figure 7. DC Current Gain, V<sub>CE</sub> = 20 V

**PNP MJE15035** 

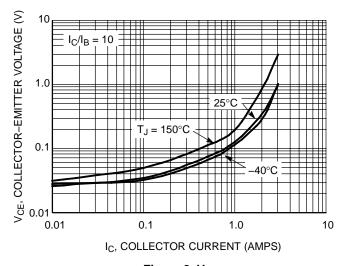
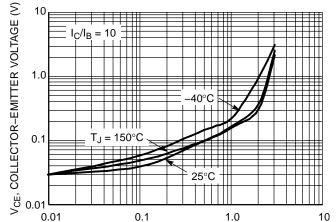


Figure 8. V<sub>CE(sat)</sub> NPN MJE15034



IC, COLLECTOR CURRENT (AMPS)

Figure 9. V<sub>CE(sat)</sub> PNP MJE15035

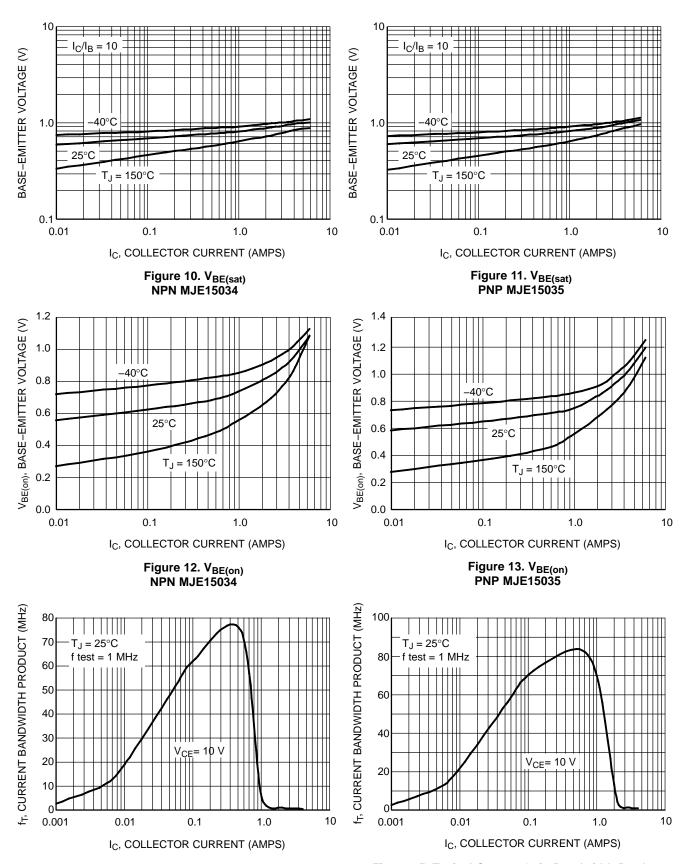


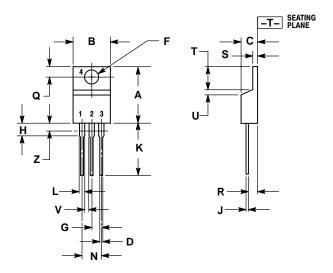
Figure 14. Typical Current Gain Bandwidth Product NPN MJE15034

Figure 15. Typical Current Gain Bandwidth Product PNP MJE15035

#### PACKAGE DIMENSIONS

# TO-220 THREE-LEAD TO-220AB

CASE 221A-09 **ISSUE AA** 



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  DIMENSION Z DEFINES A ZONE WHERE
- ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
٦	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
J	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 1:

PIN 1. BASE 2. COLLECTOR

**EMITTER** COLLECTOR

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